

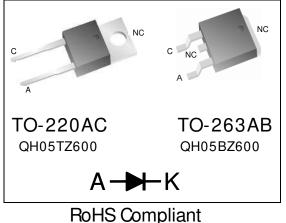
# QH05TZ600, QH05BZ600 Qspeed<sup>™</sup> Family

600 V, 5 A H-Series PFC Diode

## Product Summary

I <sub>F(AVG)</sub>	5	А
V <sub>RRM</sub>	600	V
Q <sub>RR</sub> (Typ at 125 °C)	18.9	nC
I <sub>RRM</sub> (Typ at 125 °C)	1.59	А
Softness t <sub>B</sub> /t <sub>A</sub> (Typ at 125 °C)	0.86	

## Pin Assignment



Package uses Lead-free plating and Green mold compound. Halogen free per IEC 61249-2-21.

## General Description

This device has the lowest  $Q_{\text{RR}}$  of any 600 V silicon diode. Its recovery characteristics increase efficiency, reduce EMI and eliminate snubbers.

## Applications

- Power Factor Correction (PFC) boost diode
- Motor drive circuits
- DC-AC inverters

### Features

- Low  $Q_{RR}$ , low  $I_{RRM}$ , low  $t_{RR}$
- High dI  $_{\mbox{\scriptsize F}}/\,\mbox{dt}$  capable (1000 A /  $\mbox{$\mu$s})$
- Soft recovery

## Benefits

- Increases efficiency
  - Eliminates need for snubber circuits
  - Reduces EMI filter component size & count
- Enables extremely fast switching

# Absolute Maximum Ratings

Absolute maximum ratings are the values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

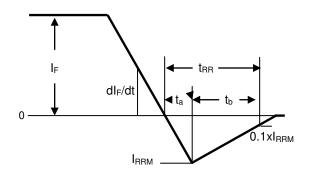
Symbol	Parameter	Conditions	Rating	Units
V <sub>RRM</sub>	Peak repetitive reverse voltage	$T_J = 25 °C$	600	V
I <sub>F(AVG)</sub>	Average forward current	$T_{\rm J} = 150 \ ^{\circ}\text{C}, \ T_{\rm C} = 109 \ ^{\circ}\text{C}$	5	Α
I <sub>FSM</sub>	Non-repetitive peak surge current	60 Hz, $\frac{1}{2}$ cycle, T <sub>C</sub> = 25 °C	50	Α
I <sub>FSM</sub>	Non-repetitive peak surge current	$^{1\!\!/_2}$ cycle of t = 28 $\mu s$ Sinusoid, T_C= 25 °C	350	А
TJ	Operating junction temperature range		-55 to 150	°C
T <sub>STG</sub>	Storage temperature		-55 to 150	°C
	Lead soldering temperature	Leads at 1.6 mm from case, 10 sec	300	°C
VISOL	Isolation voltage (leads-to-tab)	AC, TO-220	2500	V
VISOL	Isolation voltage (leads-to-tab)	AC, TO-263	1500	V
P <sub>D</sub>	Power dissipation	$T_{\rm C} = 25 ^{\circ}{\rm C}$	36.8	W

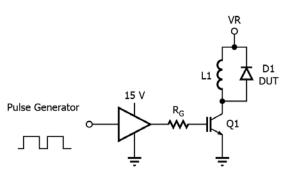
Thermal Resistance					
Symbol	Resistance from:	Conditions	Rating	Units	
$R_{\!_{ extsf{ heta}JA}}$	Junction to ambient	TO-220 (only)	62	°C/W	
$R_{\theta JC}$	Junction to case		3.4	°C/W	

# Electrical Specifications at T<sub>J</sub> = 25 °C (unless otherwise specified)

Symbol	Parameter	Conditions		Min	Тур	Max	Units
DC Chara	DC Characteristics						
		$V_{R} = 600 \text{ V},  \text{T}_{\text{J}} = 25 ^{\circ}\text{C}$		-	-	250	μA
1 <sub>R</sub>	Reverse current	$V_{R} = 600 V, T_{J} = 125$	°C	-	0.31	-	mA
VF	Forward voltage	$I_F = 5 \text{ A}, T_J = 25 \text{ °C}$		-	2.6	3.1	V
VF	Forward voltage	$I_F = 5 \text{ A}, T_J = 150 \text{ °C}$		-	2.2	-	V
CJ	Junction capacitance	$V_{R} = 10 V, 1 MHz$		-	17	-	рF
Dynamic	Dynamic Characteristics						
+	Deverse resource time	$      dI/dt = 200 \text{ A}/\mu\text{s} \\ V_\text{R}\text{=} 400 \text{ V}, \text{ I}_\text{F}\text{=} 5 \text{ A} $	T <sub>J</sub> = 25 °C	-	10	-	ns
t <sub>RR</sub>	Reverse recovery time		T <sub>J</sub> = 125 °C	-	17.4	-	ns
		$dI/dt = 200 \text{ A}/\mu\text{s}$	$T_J = 25 °C$	-	6.5	12	nC
Q <sub>RR</sub>	Reverse recovery charge	$V_{R}$ = 400 V, $I_{F}$ = 5 A	T <sub>J</sub> = 125 °C	-	18.9	-	nC
	Maximum reverse	$dI/dt = 200 \text{ A/}\mu\text{s}$	$T_J = 25 \ ^{\circ}C$	-	1.0	1.55	А
I <sub>RRM</sub>	recovery current	$V_{R}$ = 400 V, $I_{F}$ = 5 A	T <sub>J</sub> = 125 °C	-	1.59	-	А
	Softness factor = $\frac{t_B}{t_A}$	dI/dt = 200 A/µs	$T_J = 25 \ ^{\circ}C$	-	0.8	-	
S		$V_{R}$ = 400 V, $I_{F}$ = 5 A	$T_J = 125 \ ^{\circ}C$	-	0.86	-	

<u>Note to component engineers</u>: H-Series diodes employ Schottky technologies in their design and construction. Therefore, Component Engineers should plan their test setups to be similar to those for traditional Schottky test setups. (For additional details, see Application Note AN-300.)





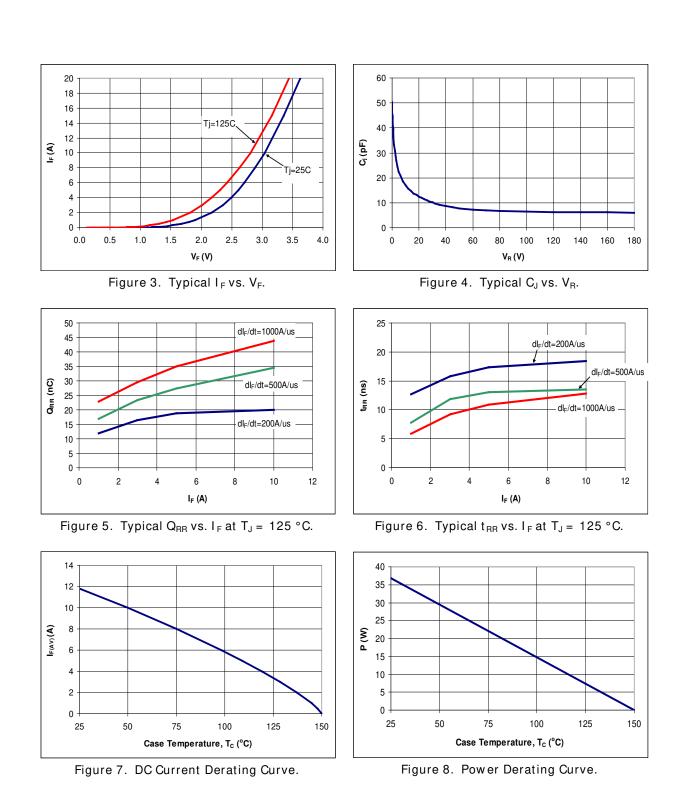
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Figure 2. Reverse Recovery Test Circuit.







## Electrical Specifications at $T_J = 25$ °C (unless otherwise specified)

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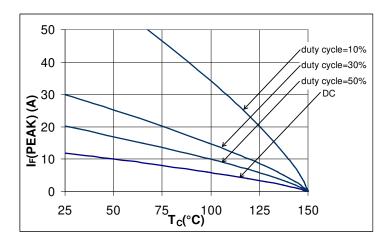


Figure 9.  $I_F(PEAK)$  vs.  $T_C$ , f = 70 kHz.

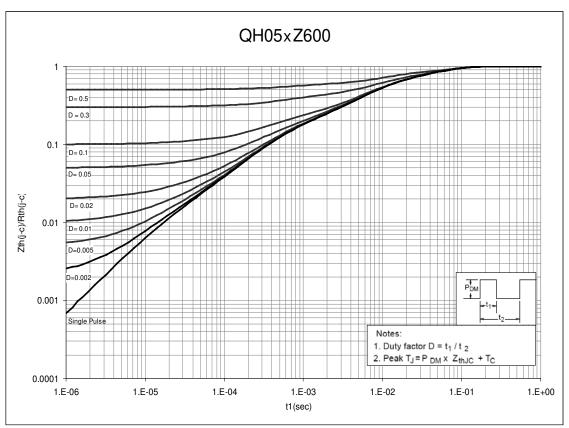


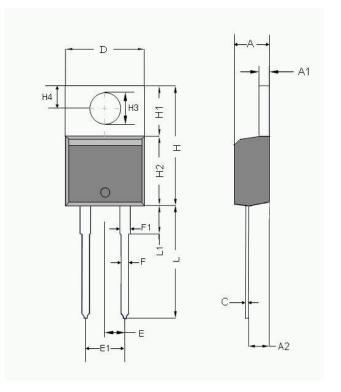
Figure 10. Normalized Maximum Transient Thermal Impedance.





# Dimensional Outline Drawings

TO-220AC



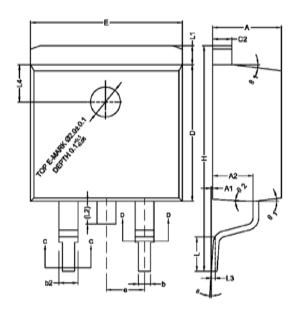
	Millimeters		
Dim	MIN	MAX	
А	4.32	4.70	
A1	1.14	1.40	
A2	2.03	2.79	
С	0.34	0.610	
D	9.65	10.67	
E	2.49	2.59	
E1	4.98	5.18	
F	0.508	1.016	
F1	1.14	1.78	
Н	14.71	16.51	
H1	5.84	6.795	
H2	8.40	9.00	
H3	3.53	3.96	
H4	2.54	3.05	
L	12.70	14.22	
L1	-	6.35	





# Dimensional Outline Drawings

### TO-263AB

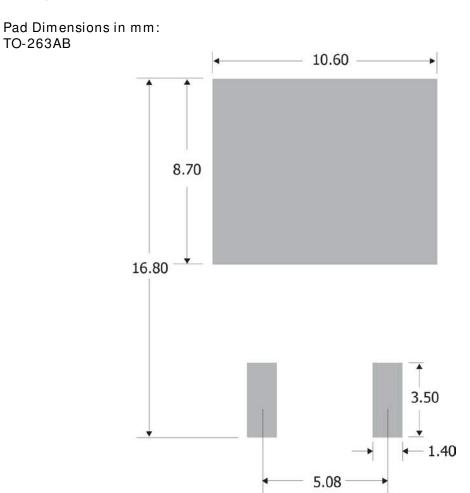


	Millimeters		
Dim	MIN	MAX	
А	4.40	4.70	
A1	0.00	0.25	
A2	2.59	2.79	
b	0.77	0.90	
b2	1.23	1.36	
c2	1.22	1.32	
D	9.05	9.25	
Е	10.06	10.26	
е	2.54 BSC	2.54 BSC	
Н	14.70	15.50	
L	2.00	2.60	
L1	1.17	1.40	
L2	-	1.75	
L3	0.25 BSC	0.25 BSC	
L4	2.00 BSC	2.00 BSC	
Θ	0°	8°	
01	5°	9°	
Θ2	1°	5°	

Mechanical Mounting Method	Maximum Torque / Pressure specification
Screw through hole in package tab	1 Newton Meter (nm) or 8.8 inch-pounds (lb-in)
Clamp against package body	12.3 kilogram-force per square centimeter (kgf/cm <sup>2</sup> ) or 175 lbf/in <sup>2</sup>







## Footprint and Solder Pad Dimensions

Soldering time and temperature: This product has been designed for use with high-temperature, lead-free solder. The component leads can be subjected to a maximum temperature of 300 °C, for up to 10 seconds. See Application Note AN-303, for more details.

## Ordering Information

Part Number	Package	Packing
QH05TZ600	TO-220AC	50 units/tube
QH05BZ600	TO-263AB	800 units/reel

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### QH05TZ600, QH05BZ600

Revision	Notes	Date
1.0	Released by Qspeed	01/10
1.1	Converted to Power Integrations Document	01/11
1.2	Added QH05BZ600	02/13
1.3	Updated with new Brand Style. Added footprint and solder pad dimension for TO-263AB package.	11/15





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